2SC458, 2SC2308

Silicon NPN Epitaxial

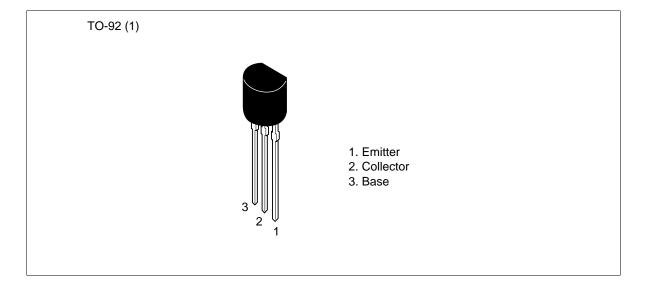
HITACHI

ADE-208-1043 (Z) 1st. Edition Mar. 2001

Application

- Low frequency amplifier
- Complementary pair with 2SA1029 and 2SA1030

Outline





2SC458, 2SC2308

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	2SC458	2SC2308	Unit
Collector to base voltage	V_{CBO}	30	55	V
Collector to emitter voltage	V _{CEO}	30	50	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I _c	100	100	mA
Emitter current	I _E	-100	-100	mA
Collector power dissipation	P _c	200	200	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

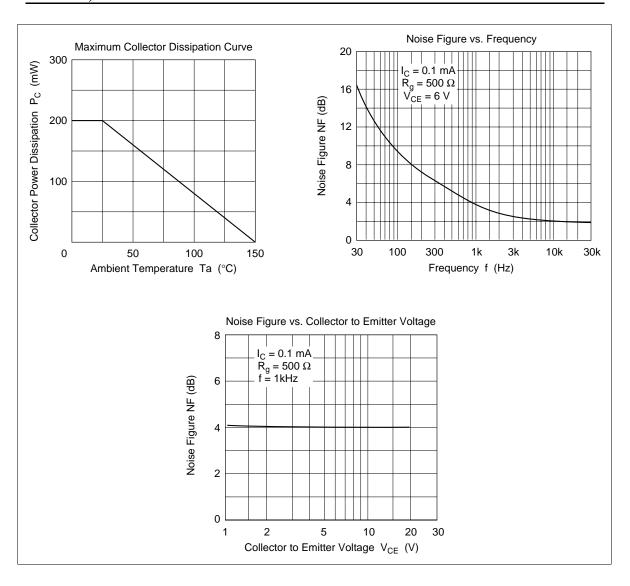
		2SC4	58		2SC2308				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	55	_	_	V	$I_{\rm C} = 10 \ \mu \text{A}, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	_	_	50	_	_	V	I_{C} = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{\text{(BR)EBO}}$	5	_	_	5	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	_	_	0.5	μΑ	$V_{CB} = 18 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	0.5	_	_	0.5	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	100	_	500	100	_	320		$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.2	_	_	0.2	V	$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 1 mA
Base to emitter voltage	V_{BE}	_	0.67	0.75		0.67	0.75	V	V_{CE} = 12 V, I_{C} = 2 mA
Gain bandwidth product	\mathbf{f}_{T}	_	230	_	_	230	_	MHz	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector output capacitance	Cob	_	1.8	3.5	_	1.8	3.5	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	4	10	_	4	10	dB	V_{CE} = 6 V, I_{C} = 0.1 mA, f = 1 kHz, R_{g} = 500 Ω
Small signal input impedance	h _{ie}	_	16.5	_	_	16.5	_	kΩ	$V_{CE} = 5V, I_{C} = 0.1 \text{mA},$ f = 270 Hz
Small signal voltage feedback ratio	h _{re}	_	70	_	_	70	_	× 10 ⁻⁶	-
Small signal current trancefer ratio	h _{fe}	_	130	_	_	130	_		-
Small signal output admittance	h _{oe}	_	11.0	_	_	11.0	_	μS	_

Note: 1. The 2SC458 and 2SC2308 are grouped by $h_{\rm FE}$ as follows.

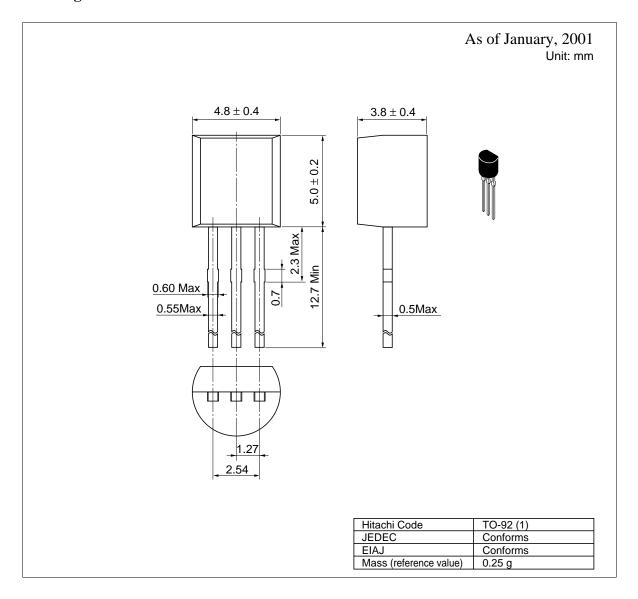
	В	С	D
2SC458	100 to 200	160 to 320	250 to 500
2SC2308	100 to 200	160 to 320	_

See characteristic curves of 2SC458 (LG) and 2SC2310 except for the followings.

2SC458, 2SC2308



Package Dimensions



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